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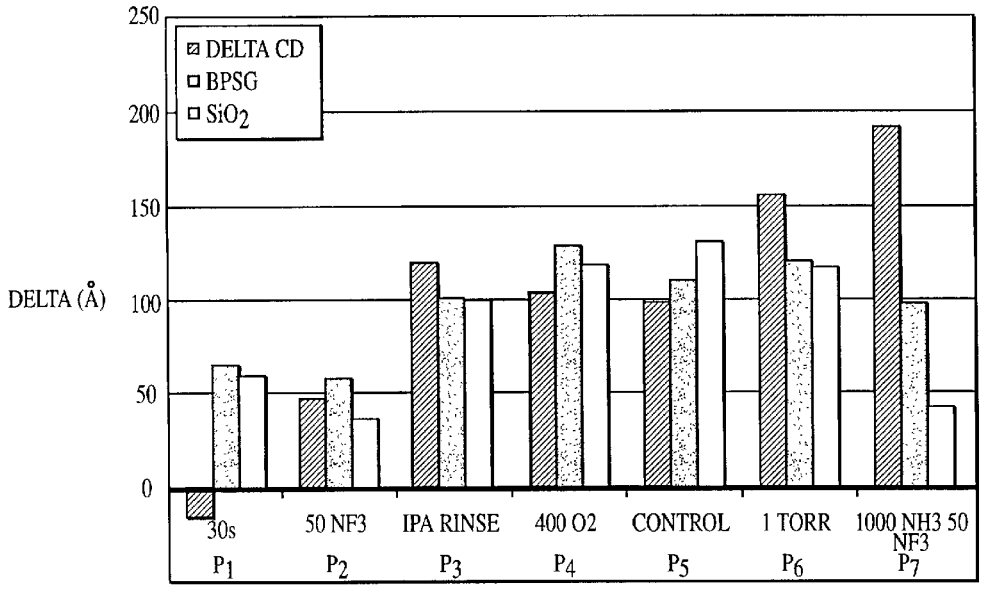
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(54) Title: METHOD FOR SELECTIVE ETCHING OF OXIDES



FUSION DRY CLEAN CD TEST

(57) Abstract: An improved dry plasma cleaning process for the removal of native oxides, or other oxide films or growth residue, from openings formed in an insulating layer provided over a semiconductor substrate, without damaging the substrate or significantly affecting the critical dimension of the opening is disclosed. A mixture of nitrogen trifluoride (NF_3), ammonia (NH_3) and oxygen (O_2) is first injected upstream into a microwave plasma source and is exited, and then the plasma is flowed downstream from the plasma source into a reaction chamber containing the substrate.

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